

Low VF Bridge Rectifiers

GBP



Features

- Glass Passivated Chip Junction
- Low IRRM
- Low VF
- High VRRM

Benefits

- Case: GBP
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor
- Reduced snubbing

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

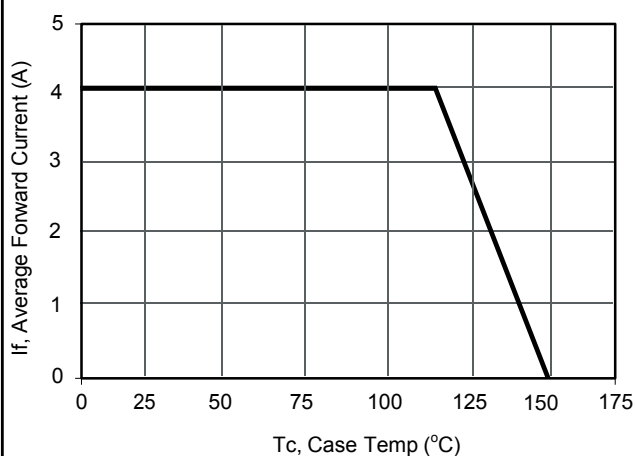
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	GBP406L	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	600	V
Maximum RMS voltage	VRMS	420	V
Maximum DC Blocking Voltage	VDC	600	V
Average Rectified Output Current	Io	4.0	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	80	A
Maximum Forward Voltage at 2.0 A	VF	0.95	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10 500	μA
Typical Junction Capacitance (Note1)	Cj	25	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C

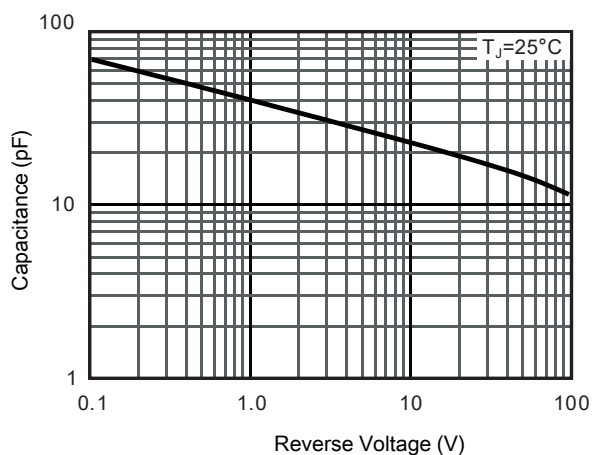
Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

2. Mounted on glass epoxy PC board with 4 × 1.5 ± 1.5 (3.81 × 3.81 cm) copper pad

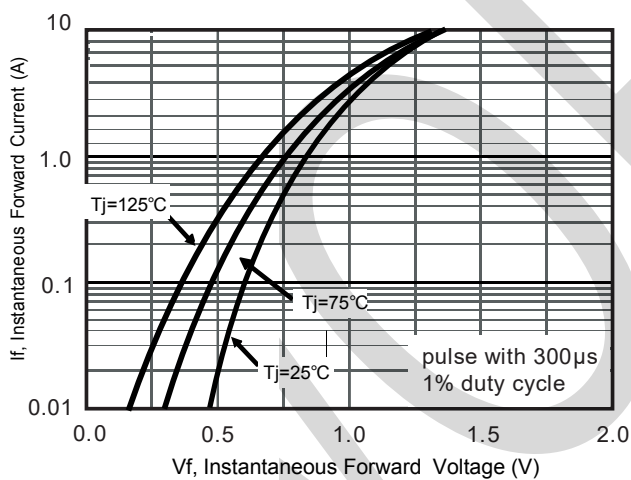
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



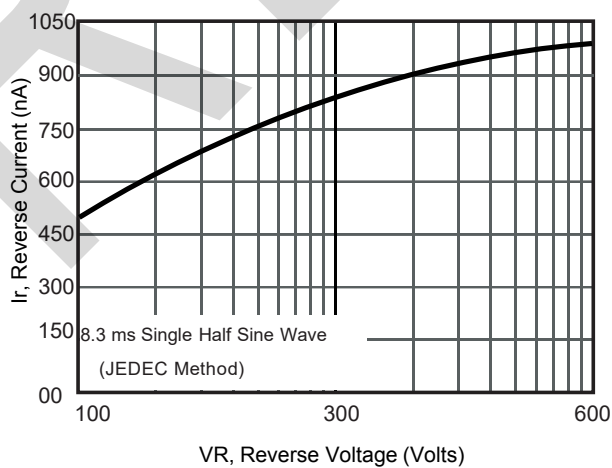
Current Derating, Case



Typical Junction Capacitance

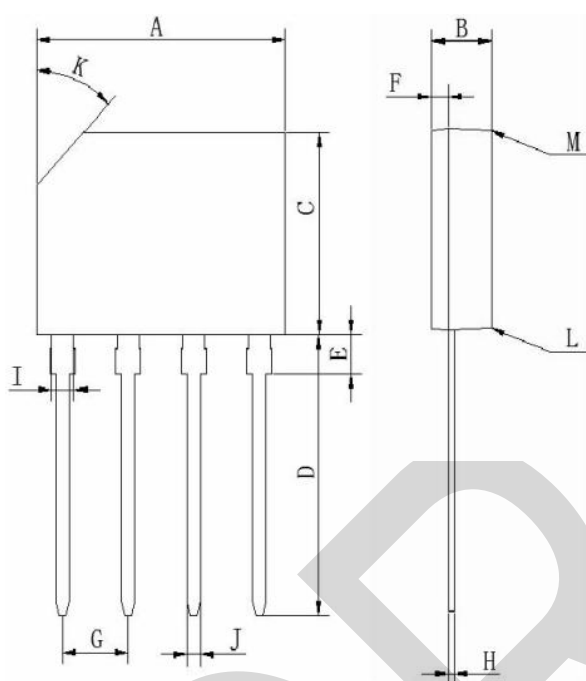


Typical Forward Voltage



Typical Reverse Current

PACKAGE OUTLINE DIMENSIONS



GBP Unit:mm		
DIM	MIN	MAX
A	14.25	14.75
B	3.35	3.65
C	10.2	10.6
D	14.3	14.8
E	1.8	2.2
F	0.8	1.1
G	3.56	4.06
H	0.3	0.55
I	1.22	1.42
J	0.76	0.86
K	2.7X45°(Typ.)	
L	-	3°
M	-	3°
All Dimensions in millimeter		

